

ABSTRACT OF THE DISCLOSURE

According to the present invention, a dummy wafer is formed by forming a masking film on a rear surface of a silicon wafer; spray coating aluminum and depositing an aluminum film on a front surface of the silicon wafer; spray coating ceramics or carbon and depositing a ceramic film or carbon film on the aluminum film so that the aluminum film may be completely covered; and removing the masking film formed on the rear surface. Also, a dummy wafer can be formed by using an aluminum wafer as a wafer substrate and subjecting it to anodic oxidation to form a film of aluminum oxide.